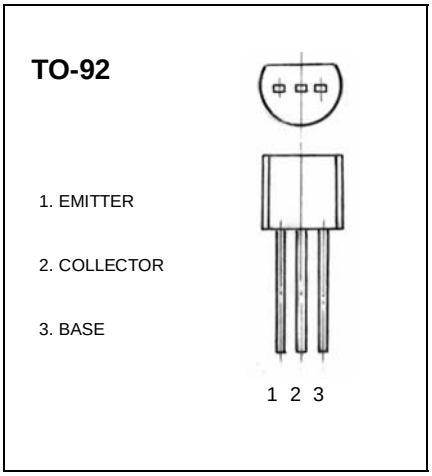
Transys Electronics LIMITED

TO-92 Plastic-Encapsulated Transistors

2SA950 TRANSISTOR (PNP)



FEATURE

Power dissipation

P_{CM}: 0.6 W (Tamb=25℃)

Collector current

I_{CM} : -0.8 A

Collector-base voltage

$V_{(BR)CBO}$: -35 V

Operating and storage junction temperature range

T_j, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= -1mA , I_E=0	-35			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= -10 mA , I_B=0	-30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -1Ma, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}= -35V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V, I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V, I_C=-100mA	100		320	
	$h_{FE(2)}$	V_{CE}=-1V, I_C= -700mA	35			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -500mA, I_B= -20mA			-0.7	V
Collector Output Capacitance	Cob	VCB=-10V, IE=0 f=1MHz		19		pF
Transition frequency	f_T	V_{CE}=-5V, I_C=-10mA,		120		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320